MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TK3R2A10PL

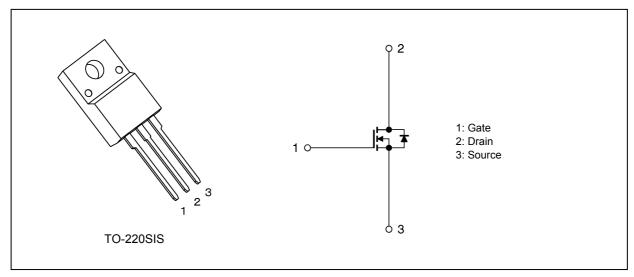
### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 48 \text{ nC}$  (typ.)
- (3) Small output charge:  $Q_{oss} = 164 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 2.6 \text{ m}\Omega$  (typ.) (V<sub>GS</sub> = 10 V)
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 100 \ V)$
- (6) Enhancement mode:  $V_{th}$  = 1.5 to 2.5 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristi	cs		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	100	V
Gate-source voltage			V <sub>GSS</sub>	±20	]
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 1)	Ι <sub>D</sub>	100	Α
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι <sub>D</sub>	106	A
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I <sub>DP</sub>	500	A
Power dissipation	(T <sub>c</sub> = 25 °C)		PD	54	W
Single-pulse avalanche energy		(Note 3)	E <sub>AS</sub>	278	mJ
Single-pulse avalanche current		(Note 3)	I <sub>AS</sub>	86	A
Channel temperature			T <sub>ch</sub>	175	ů
Storage temperature			T <sub>stg</sub>	-55 to 175	°C
Isolation voltage (RMS)	(t = 1.0 s)		VISO(RMS)	2000	V
Mounting torque			TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### 5. Thermal Characteristics

Characteristic	S	Symbol	Max	Unit
Channel-to-case thermal resistance	(T <sub>c</sub> = 25 °C)	R <sub>th(ch-c)</sub>	2.77	°C/W
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	R <sub>th(ch-a)</sub>	62.5	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Limited 100 A by package capability.

Note 3:  $V_{DD}$  = 80 V,  $T_{ch}$  = 25 °C (initial), L = 29  $\mu$ H, I<sub>AS</sub> = 86 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

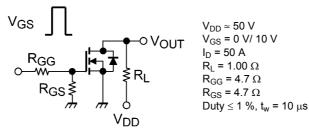
## 6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	_	—	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	100	—	_	V
Drain-source breakdown voltage (Note 4)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	65	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	_	2.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 A		3.1	4.3	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A	_	2.6	3.2	

Note 4: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	9500	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	65	—	
Output capacitance	C <sub>oss</sub>		_	1500	_	
Gate resistance	r <sub>g</sub>	—	_	2.2	_	Ω
Switching time (rise time)	tr	See Fig. 6.2.1	_	22	—	ns
Switching time (turn-on time)	t <sub>on</sub>		_	46	_	
Switching time (fall time)	t <sub>f</sub>	]	_	46	_	
Switching time (turn-off time)	t <sub>off</sub>		_	147	_	



#### Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD}\approx 50~V,~V_{GS} \text{ = } 10~V,~I_{D} \text{ = } 50~\text{A}$	_	161	_	nC
gate-drain)		$V_{DD} \approx 50 \text{ V}, \text{ V}_{GS} \text{ = } 4.5 \text{ V}, \text{ I}_{D} \text{ = } 50 \text{ A}$	_	83		
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 50$ V, $V_{GS}$ = 10 V, $I_D$ = 50 A	_	30	_	
Gate-drain charge	Q <sub>gd</sub>		_	37	_	
Gate switch charge	Q <sub>SW</sub>		_	48	_	
Output charge	Q <sub>oss</sub>	$V_{DS}$ = 50 V, $V_{GS}$ = 0 V, f = 1 MHz		164	_	

### 6.4. Source-Drain Characteristics ( $T_a = 25 \ ^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 5)	I <sub>DRP</sub>	t = 100 μs	_	_	500	A
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 100 A, V <sub>GS</sub> = 0 V	_	—	-1.5	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 25 A, V <sub>GS</sub> = 0 V,	_	75	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 100 A/μs		150	_	nC

Note 5: Ensure that the channel temperature does not exceed 175 °C.

### 7. Marking (Note)

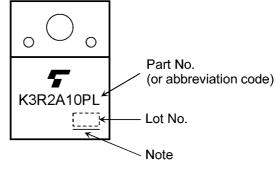


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

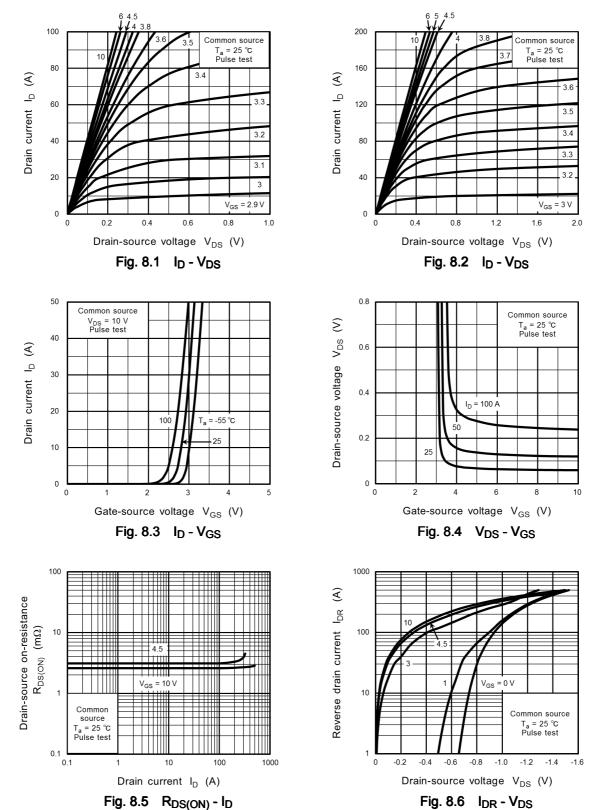
Not underlined: [[Pb]]/INCLUDES > MCV

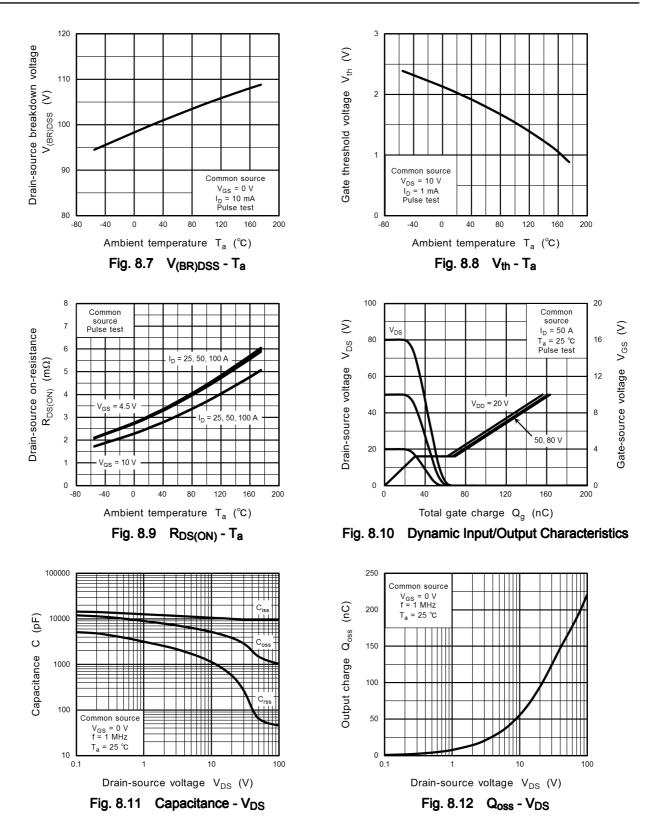
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

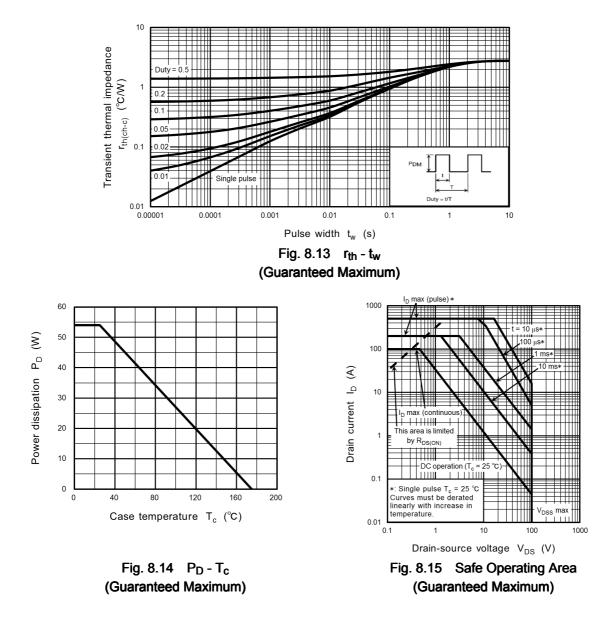
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### 8. Characteristics Curves (Note)





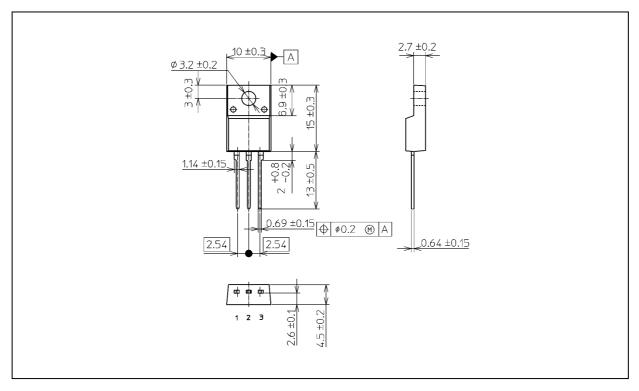


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## TK3R2A10PL

### **Package Dimensions**

Unit: mm



#### Weight: 1.7 g (typ.)

	Package Name(s)
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	

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